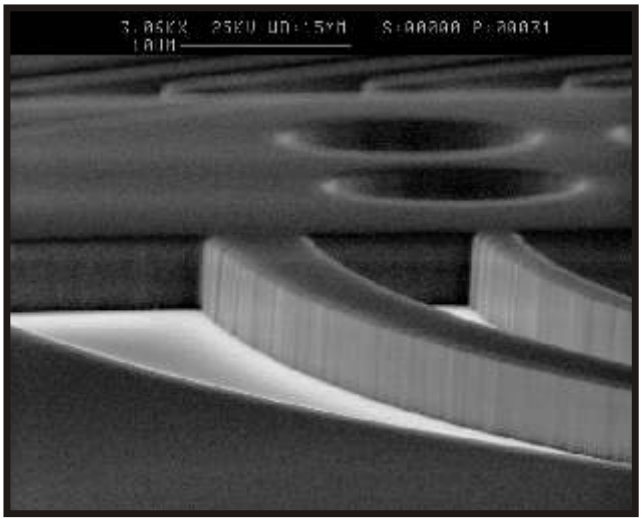
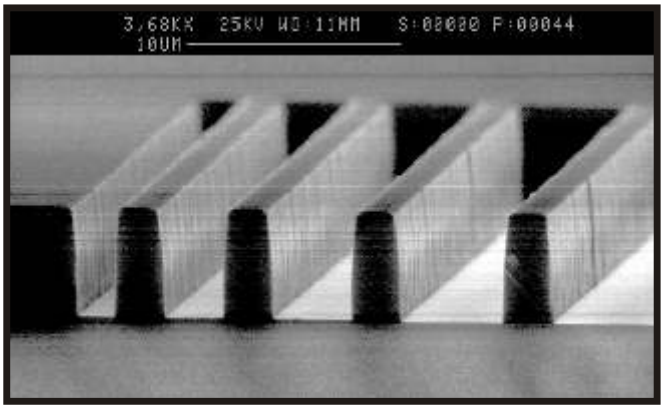
email: plasma@oxford.de

Plasmalab Data

AlGaN/ GaN ICP Etching





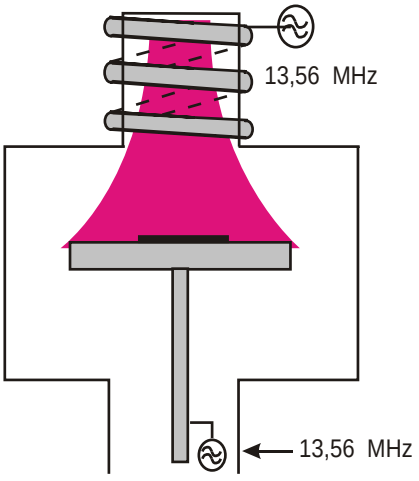
OPT application lab:
10 µm deep AlGaN/ GaN etch

OPT application lab:
8 µm deep etch

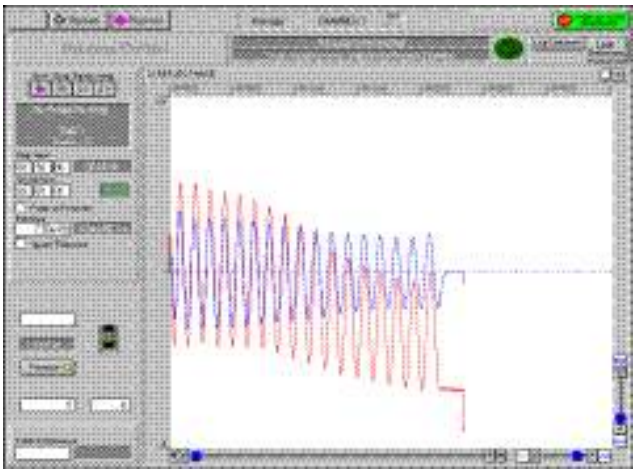
Plasmalab 80 Plus

Plasmalab System 100

Plasmalab System 133



OPT application lab:
laser endpoint scan from GaN etch



Technology:

Reactive Ion Etching
with ICP Source (2 or 13 MHz)
Inductive Coupled Plasma
RF driven substrate electrode
Cl based processes

Results:

rate: 0.5 - 1 µm/ min with SiO2 mask
0.3 µm/ min with photoresist mask
selectivity to SiO2 5 - 10 : 1, to PR 1.15 : 1
anisotropic profile
clean etch surface
low ion induced damage